

Title (en)
Capacitor structure

Title (de)
Kondensatorstruktur

Title (fr)
Structure de condensateur

Publication
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Application
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Abstract (en)
The invention relates to a capacitor structure (2) comprising a silicon substrate (4) with first and second sides (6, 8), a trench capacitor (10) including a basis electrode (12), a multilayer stack comprising at least one of an even elementary sequence of layers and/or one of an odd elementary sequence of layers, wherein an even/odd elementary sequence of layers comprises an insulator layer (16, 20), an even/odd conductive layer (18, 22); and comprising a second pad (26) and a fourth pad (30) coupled to the basis electrode (12), a first pad (24) and a third pad (28) coupled together, the first pad (24) being located on the same substrate side than the second pad (26), the third pad (28) being located on the same substrate side than the fourth pad (30), the third pad (28) being coupled to an even conductive layer (18), said even conductive layer (18) being flush with or protruding from the opposite second side (8).

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